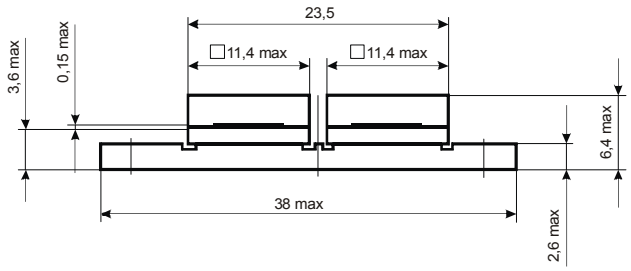
Syntez Microelectronics

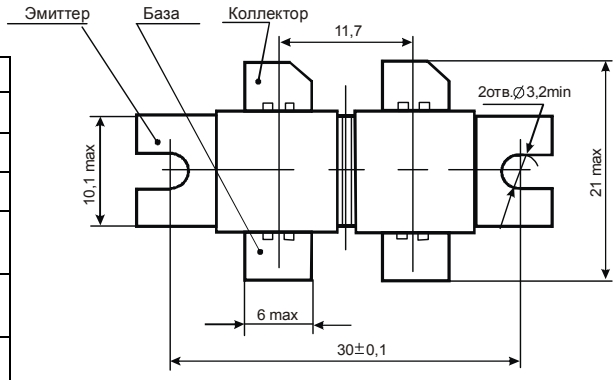
KT9174A

NPN SILICON RF POWER TRANSISTOR

Designed for operation in linear Class AB push-pull power amplifiers of TV and aircraft radio transmitters

- Output power = 300 W
- Power gain = 12 dB (min), f = 100 MHz





Case KT-82

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	55	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	28	A
Operating Junction Temperature	T_j	+200	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	0.5	°C/W
Total Power Dissipation, T_C=25 °C	P_D	350	W

FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain (V_{cc} = 28 V, P_{out} = 300 W @ 1 dB Comp., f = 100 MHz)	G_P	12			dB
Collector Efficiency (V_{cc} = 28 V, P_{out} = 300 W, f = 100 MHz)	η_c	55			%

ZAO 'Syntez Microelectronics'

119V Leninsky Prospekt, Voronezh 394007, Russia • Tel +7-4732-379-101 Fax +7-4732-266-057

exim@syntezmicro.ru www. syntezmicro.ru

Specification is subject to change without notice